

Please replace the paragraph abridging pages 8 and 9, with the following rewritten paragraph:

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10029145-12801  
-- As shown in FIG. 3A, a material for forming a gate line (100) is deposited on a glass substrate 11 as a single film of Cu or Cu/Ti, or as a deposition film sequentially formed of Cu and Cu/Ti by using sputtering or other techniques. Then, photolithography is performed to form the gate line, a gate electrode 12a and a gate pad 12b. A gate insulating film 13 made of a silicon nitride film, silicon oxide film, etc. is formed on the entire surface of the glass substrate 11 including the gate electrode 12a and the gate pad 12b. Although the glass substrate 11 is preferred as a substrate, the substrate may be formed with other materials.--

Please replace the paragraph beginning on page 10, line 19, with the following rewritten paragraph:

A3  
-- FIG. 4A to FIG. 4D are sectional views showing manufacturing process steps of the LCD device according to the embodiment of the present invention, taken along lines III-III' (TFT region) and V-V' (data pad region) of FIG. 3.--